onsemi

General Purpose Transistor PNP Silicon MMBT3906L, SMMBT3906L

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-40	Vdc
Collector – Base Voltage	V _{CBO}	-40	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-200	mAdc
Collector Current – Peak (Note 3)	I _{CM}	-800	mAdc

THERMAL CHARACTERISTICS

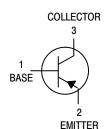
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board (Note 1) @ T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

3. Reference SOA curve.





SOT-23 (TO-236) CASE 318 STYLE 6



2A = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

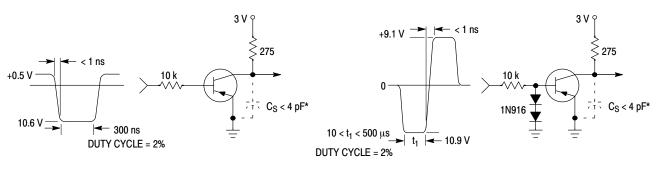
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characte	ristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$		V _{(BR)CEO}	-40	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \ \mu Adc, I_E = 0)$		V _{(BR)CBO}	-40	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_C = 0$)		V _{(BR)EBO}	-5.0	_	Vdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		I _{BL}	_	-50	nAdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		ICEX	_	-50	nAdc
ON CHARACTERISTICS (Note 4)					
$\begin{array}{l} \text{DC Current Gain} \\ (I_C = -0.1 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -1.0 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -50 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \end{array}$		H _{FE}	60 80 100 60 30	- - 300 - -	_
$\begin{array}{l} \mbox{Collector}-\mbox{Emitter Saturation Voltage} \\ (I_C = -10 \mbox{ mAdc}, \mbox{I}_B = -1.0 \mbox{ mAdc}) \\ (I_C = -50 \mbox{ mAdc}, \mbox{I}_B = -5.0 \mbox{ mAdc}) \end{array}$		V _{CE(sat)}		-0.25 -0.4	Vdc
$\begin{array}{l} \text{Base-Emitter Saturation Voltage} \\ (I_{C} = -10 \text{ mAdc}, I_{B} = -1.0 \text{ mAdc}) \\ (I_{C} = -50 \text{ mAdc}, I_{B} = -5.0 \text{ mAdc}) \end{array}$		V _{BE(sat)}	-0.65 -	-0.85 -0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS			1		
Current – Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –20 Vdc, f =	100 MHz)	fT	250	_	MHz
Output Capacitance (V _{CB} = -5.0 Vdc, I _E = 0, f = 1.0 MHz	z)	C _{obo}	_	4.5	pF
Input Capacitance ($V_{EB} = -0.5$ Vdc, $I_C = 0$, f = 1.0 MHz	z)	C _{ibo}	_	10	pF
Input Impedance (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f =	= 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f =	= 1.0 kHz)	h _{re}	0.1	10	X 10 ⁻⁴
Small – Signal Current Gain (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f =	= 1.0 kHz)	h _{fe}	100	400	-
Output Admittance ($I_C = -1.0$ mAdc, $V_{CE} = -10$ Vdc, f =	= 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure (I _C = $-100 \ \mu$ Adc, V _{CE} = $-5.0 \ V$ dc, R	_S = 1.0 kΩ, f = 1.0 kHz)	NF	_	4.0	dB
SWITCHING CHARACTERISTICS			•	·	
Delay Time		td	_	35	

Delay Time	(V _{CC} = -3.0 Vdc, V _{BE} = 0.5 Vdc,	t _d	-	35	20	
Rise Time	$I_{\rm C} = -10$ mAdc, $I_{\rm B1} = -1.0$ mAdc)	t _r	-	35	ns	
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc},$	t _s	-	225	ns	Ī
Fall Time	I _{B1} = I _{B2} = −1.0 mAdc)	t _f	-	75	115	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

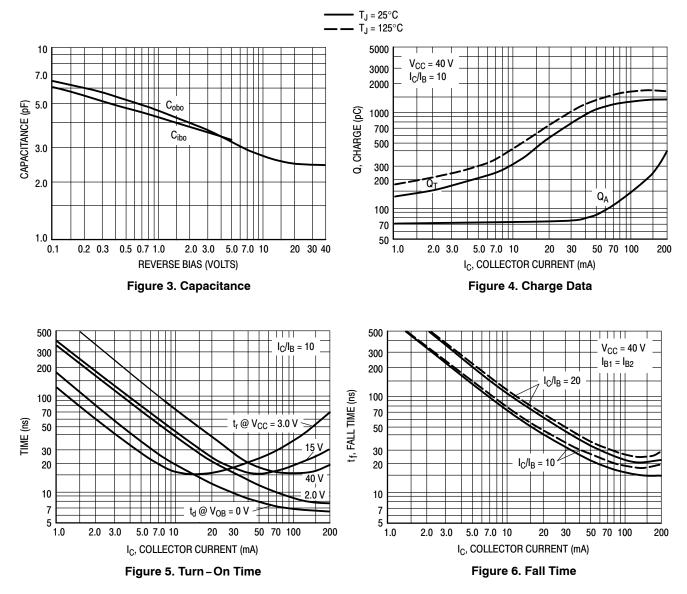


* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

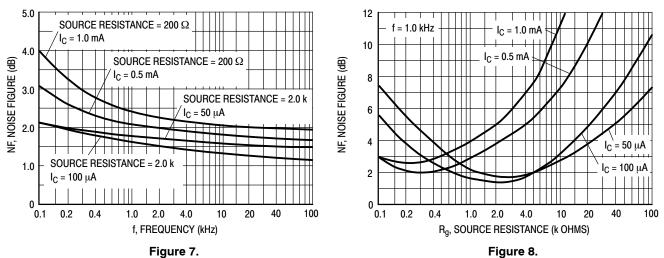
Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



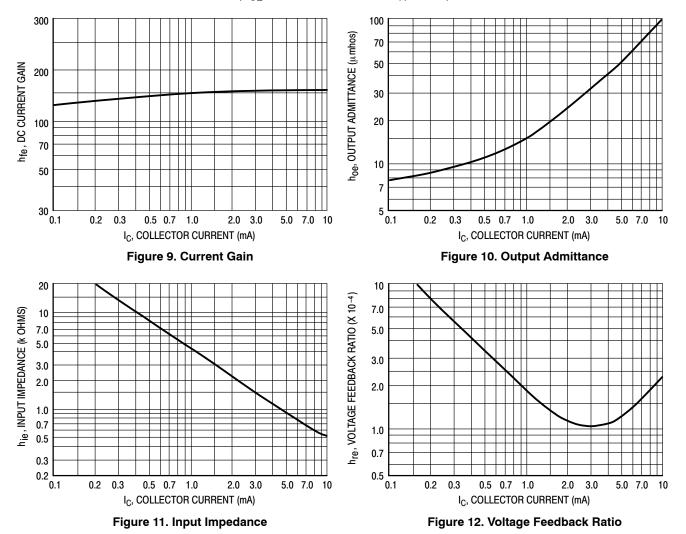


(V_{CE} = -5.0 Vdc, T_A = 25° C, Bandwidth = 1.0 Hz)









TYPICAL STATIC CHARACTERISTICS

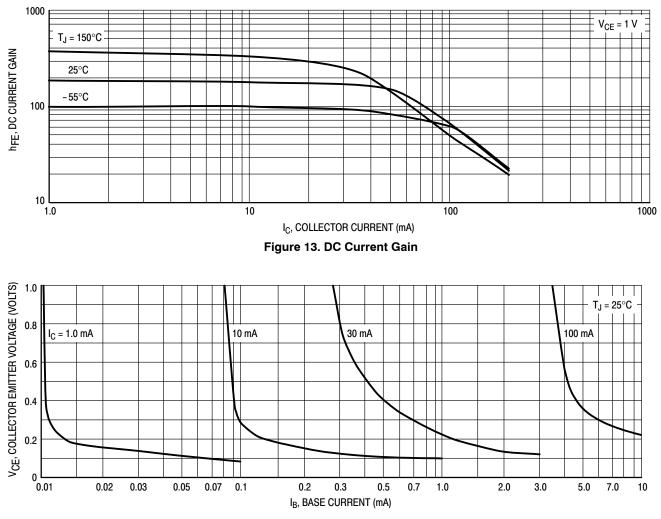


Figure 14. Collector Saturation Region

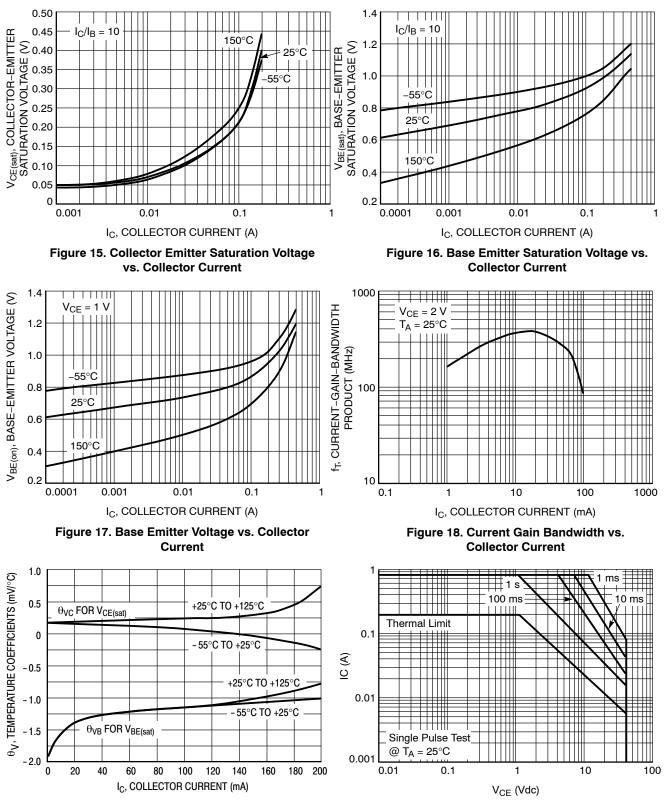


Figure 19. Temperature Coefficients

Figure 20. Safe Operating Area

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

ISSUE AU

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS					
DIM	MIN	NOM	МАХ		
А	0.89	1.00	1.11		
A1	0.01	0.06	0.10		
b	0.37	0.44	0.50		
с	0.08	0.14	0.20		
D	2.80	2.90	3.04		
E	1.20	1.30	1.40		
е	1.78	1.90	2.04		
L	0.30	0.43	0.55		
L1	0.35	0.54	0.69		
Ηe	2.10	2.40	2.64		
Т	0°		10°		

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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